

however, the figure captions are correctly numbered.

Intrinsic Diffusion of Boron and Phosphorus in Silicon Free from Surface Effects, R. N. Ghosh-tagore [Phys. Rev. B **3**, 389 (1971)]. Typesetting errors occurred in the third and fourth sentences of the abstract during the galley-correcting process. The correct abstract is as follows.

Boron and phosphorus were diffused in either hydrogen or pure-argon atmosphere into float-zoned, epitaxial, and oxygen-doped (111) silicon from a 4-12- μ -thick epitaxial-doped silicon surface layer. Under intrinsic conditions, the concentration profiles obtained show Fickian behavior at

all surface and bulk concentration conditions. Between 1130 and 1405 °C, the intrinsic diffusivities can be described by $D_P = 7.4 \times 10^{-2} \exp[(-3.30 \pm 0.03 \text{ eV})/kT] \text{ cm}^2/\text{sec}$ and $D_B = 2.1 \times 10^{-3} \exp[(-2.85 \pm 0.05 \text{ eV})/kT] \text{ cm}^2/\text{sec}$. Compared with earlier studies using oxide diffusion sources, the diffusion coefficients of both boron and phosphorus are found to be considerably smaller. Moreover, above 1130 °C they are independent of surface concentration ($\leq 3 \times 10^{19} \text{ cm}^{-3}$), bulk conductivity type (n or p) and level (6×10^{13} – $8 \times 10^{18} \text{ cm}^{-3}$), surface-to-bulk concentration ratio (~ 1 – 3.3×10^5), and oxygen concentration (to 10^{18} cm^{-3}). In the light of some related work, the present results are shown to indicate the true bulk-diffusion process in silicon.